

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
60	2.5 at $V_{GS} = 10$ V	0.25
	3 at $V_{GS} = 4.5$ V	0.23
	8 at $V_{GS} = 3$ V	0.05

FEATURES

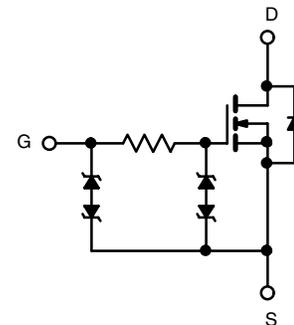
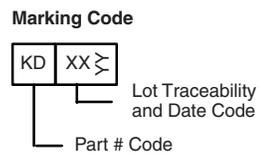
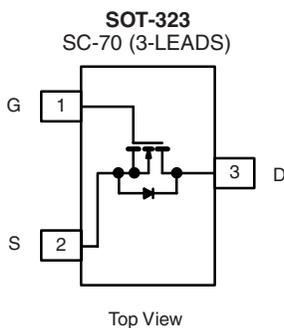
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- P-Channel Driver
- Notebook PC
- Servers



Ordering Information: Si1330EDL-T1-E3 (Lead (Pb)-free)
Si1330EDL-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	60		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	0.25	0.24	A
		$T_A = 70$ °C	0.2	0.19	
Pulsed Drain Current	I_{DM}	1.0			
Continuous Source Current (Diode Conduction) ^a	I_S	0.26	0.23		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	0.31	0.28	W
		$T_A = 70$ °C	0.20	0.18	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 5$ s	355	400	°C/W
		Steady State	380	450	
Maximum Junction-to-Foot (Drain)	R_{thJF}	285	340		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

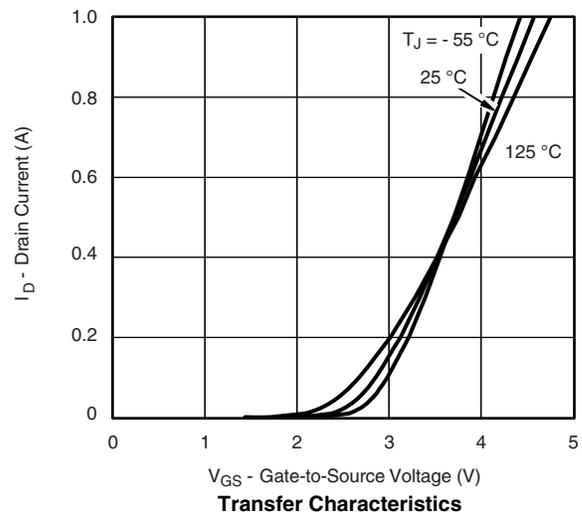
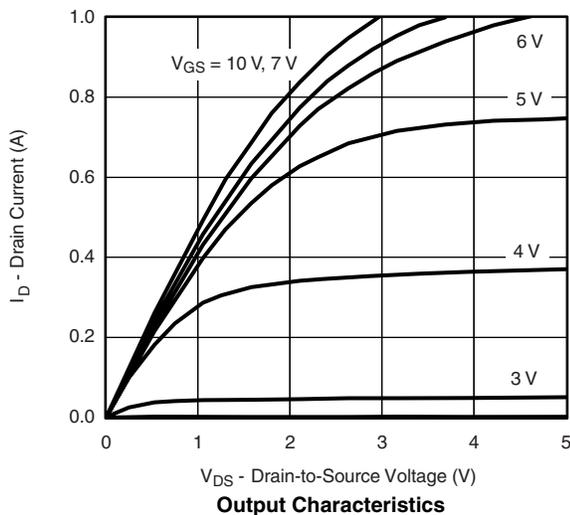
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted ^a						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 10\text{ }\mu\text{A}$	60			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	2.0	2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			1 10	
On-State Drain Current ^b	$I_{D(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 7.5\text{ V}$	0.5			A
		$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}$	0.4			
		$V_{GS} = 3\text{ V}, V_{DS} = 10\text{ V}$	0.05			
Drain-Source On-Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 0.25\text{ A}$		1.0	2.5	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 0.2\text{ A}$		1.4	3	
		$V_{GS} = 3\text{ V}, I_D = 0.025\text{ A}$		3.0	8	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 0.25\text{ A}$		350		mS
Diode Forward Voltage	V_{SD}	$I_S = 0.23\text{ A}, V_{GS} = 0\text{ V}$		0.83	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}$ $I_D \cong 0.25\text{ A}$		0.4	0.6	nC
Gate-Source Charge	Q_{gs}			0.11		
Gate-Drain Charge	Q_{gd}			0.15		
Gate Resistance	R_g			173		Ω
Turn-On Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 150\text{ }\Omega$ $I_D \cong 0.2\text{ A}, V_{GEN} = 10\text{ V}$ $R_g = 10\text{ }\Omega$		3.8	10	ns
	t_r			4.8	15	
Turn-Off Time	$t_{d(off)}$			12.8	20	
	t_f			9.6	15	

Notes:

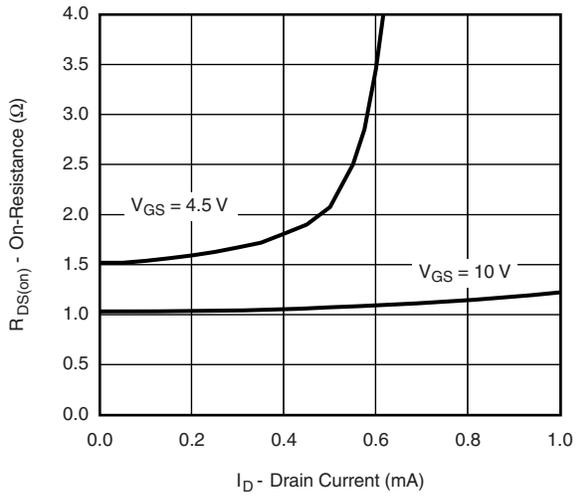
- a. Pulse test: $PW \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

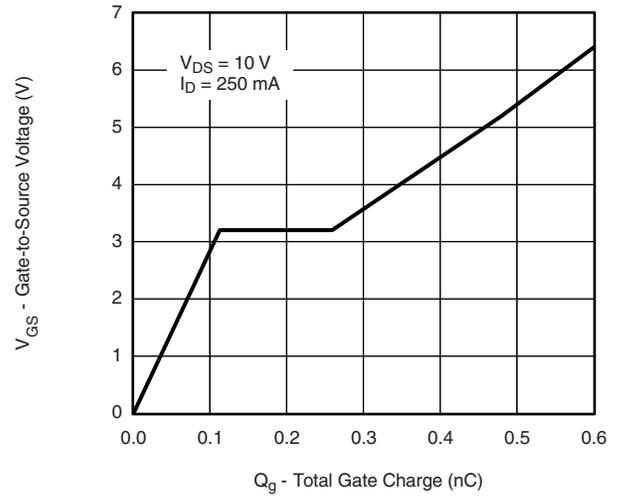
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



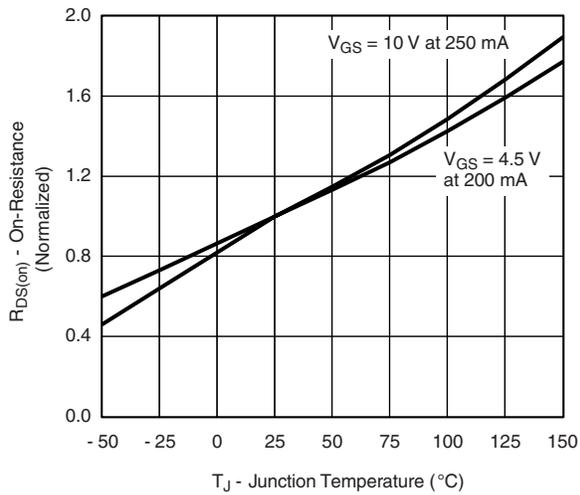
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



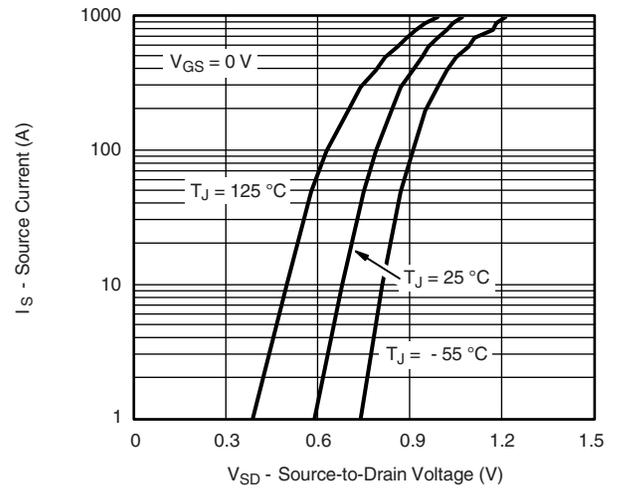
On-Resistance vs. Drain Current



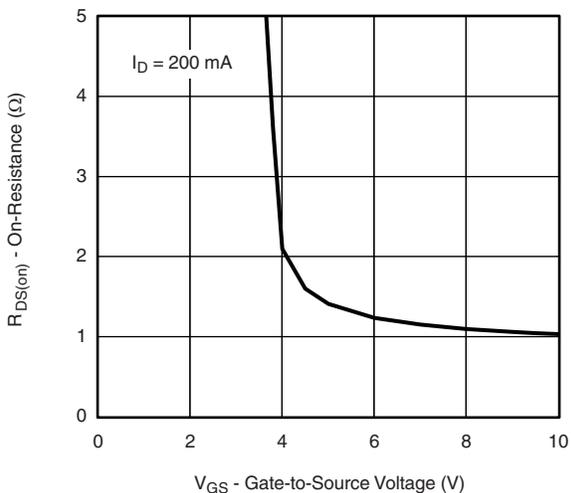
Gate Charge



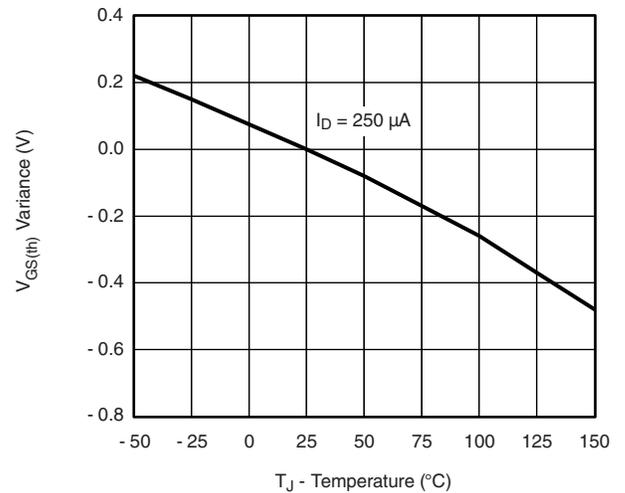
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

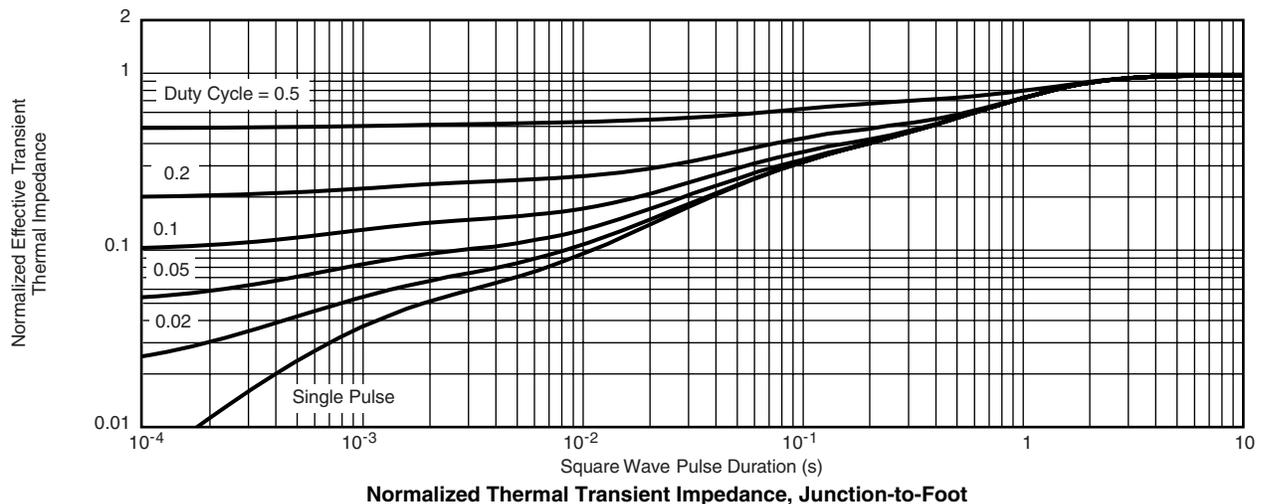
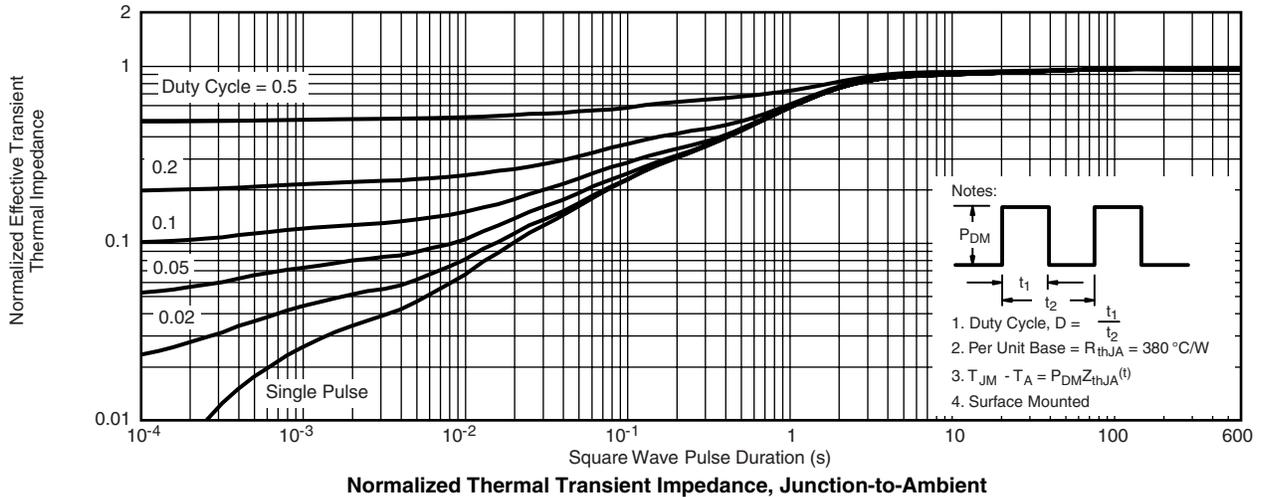
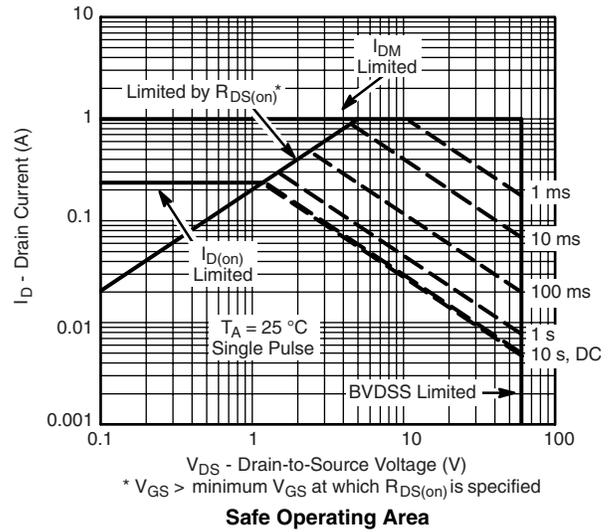
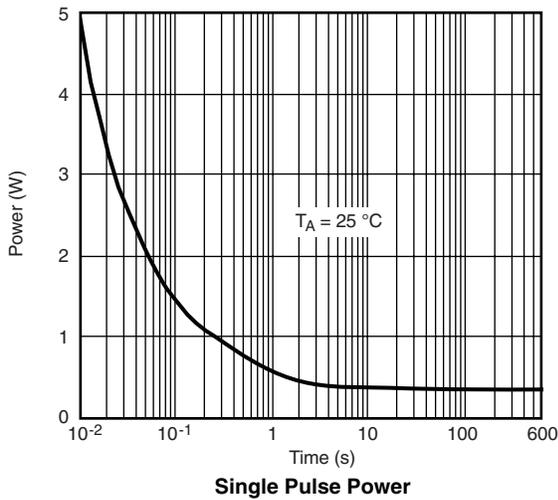


On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance over Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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